

FDD2582 Information



For Reference Only

Part Number FDD2582

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 150V 21A DPAK **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

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FDD2582 Specifications

Manufacturer Part NumberFDD2582ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesPowerTrench?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C3.7A (Ta), 21A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1295pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)95W (Tc)Rds On (Max) @ Id, Vgs66 mOhm @ 7A, 10V		
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Input Capacitance (Ciss) (Max) @ Vds 1295pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 95W (Tc) Rds On (Max) @ Id, Vgs 66 mOhm @ 7A, 10V	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 95W (Tc) Rds On (Max) @ Id, Vgs 66 mOhm @ 7A, 10V	Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
FET Feature - Power Dissipation (Max) 95W (Tc) Rds On (Max) @ Id, Vgs 66 mOhm @ 7A, 10V	Input Capacitance (Ciss) (Max) @ Vds	1295pF @ 25V
Power Dissipation (Max) 95W (Tc) Rds On (Max) @ Id, Vgs 66 mOhm @ 7A, 10V	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 66 mOhm @ 7A, 10V	FET Feature	-
	Power Dissipation (Max)	95W (Tc)
On anti- Town anti-	Rds On (Max) @ Id, Vgs	66 mOhm @ 7A, 10V
Operating Temperature -55°C ~ 1/5°C (13)	Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package TO-252AA	Supplier Device Package	TO-252AA
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

FDD2582 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDD2582 Payment Methods





















FDD2582 Shipping Methods













If you have any question about FDD2582, please do not hesitate to contact us!

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